

Features:

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

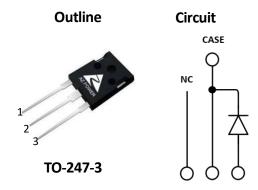
Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit
V_{RRM}	650	V
I _F (Tc=144ºC)	25	А
Qc	68	nC

Applications:

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters



Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions
V_R	DC Peak Reverse Voltage	650	V	T _J =25°C
V_{RRM}	Repetitive Peak Reverse Voltage	650	V	T _J =25°C
V_{RSM}	Surge Peak Reverse Voltage	650	V	T _J =25°C
I _F	Continuous Forward Current	66 29 25	А	T _C =25°C T _C =135°C T _C =144°C
I _{FRM}	Repetitive Peak Forward Surge Current	176 160	А	T_{C} =25°C, T_{P} =10ms, Half Sine Wave T_{C} =125°C, T_{P} =10ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	236 212	А	T_C =25°C, T_P =10ms, Half Sine Wave Tc=125°C, T_P =10ms, Half Sine Wave
P _D	Power Dissipation	211 70	W	T _C =25°C Tc=125°C
$T_{J,max}$	Operating Junction Temperature	175	°C	
T _{stg}	Storage Temperature Range	-55 to 175	°C	

S4D065V025S, Rev. 0.b Page 1 of 4



Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
R _{thJC}	Thermal Resistance		0.71		°C/W

Electrical Characteristics

Symbol Parameter	Devenuenteur	Value		1114	Test Conditions	
	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V_{DC}	DC Blocking Voltage	650			V	I _R =500μA, Τ _J =25°C
V	Forward Voltage		1.45	1.7	٧	I _F =25A, T _J =25°C
V _F	Forward Voltage		1.75	2.0		I _F =25A, T _J =175°C
	Samuel Commit		2	50	μΑ	V _R =650V, T _J =25°C
I _R F	Reverse Current		50	300		V _R =650V, T _J =175°C
Q _C Total Capacitive	Tabal Canasitina Channa		68		nC	I _F =25A, dI/dt=600A/μs
	iotai Capacitive Charge					T _J =25°C, V _R =400V
С	Total Capacitance		796			V _R =1V, T _J =25°C, f=1 MHz
			157		рF	V_R =200V, T_J =25°C, f=1 MHz
			138			V _R =400V, T _J =25°C, f=1 MHz

Typical Performance

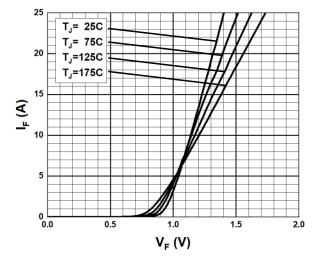


Fig. 1 Forward Characteristics

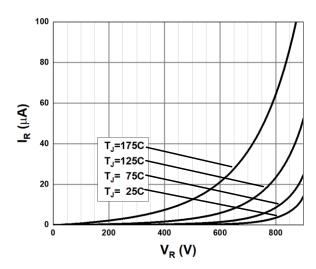
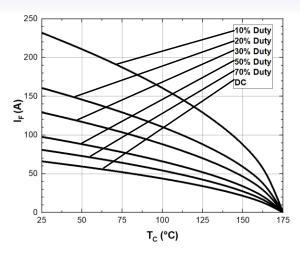


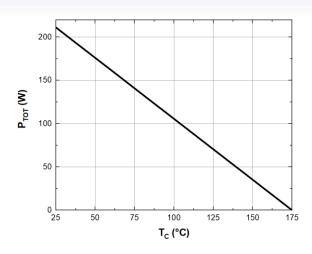
Fig. 2 Reverse Characteristics

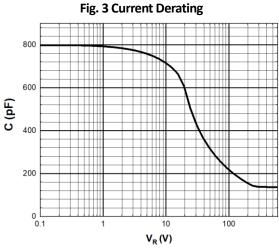
S4D065V025S, Rev. 0.b Page 2 of 4

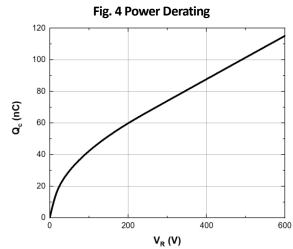


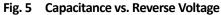
Typical Performance

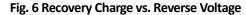


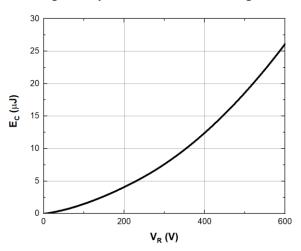












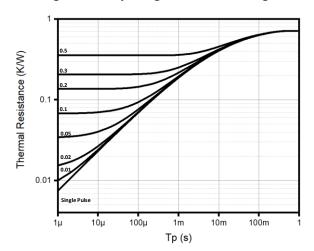


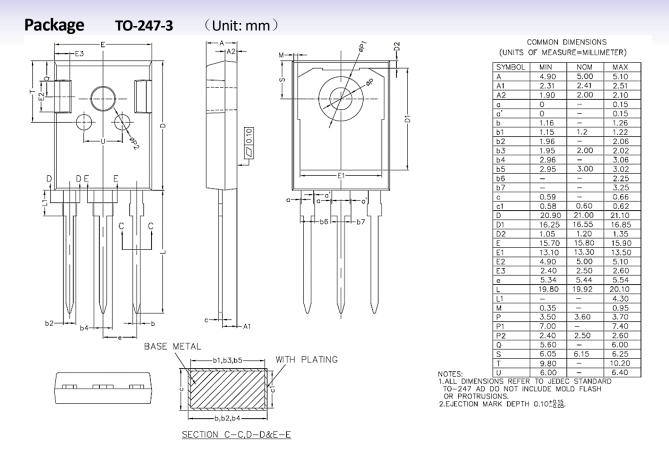
Fig. 7 Capacitance stored Energy

Fig. 8 Thermal Impedance

Page 3 of 4

S4D065V025S, Rev. 0.b





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S4D065V025S, Rev. 0.b